

AMENDMENTS TO THE SPECIFICATION AND ABSTRACT

Please replace the paragraph beginning at line 10 on page 1 of the substitute specification with the following rewritten paragraph.

In an interlayer film CMP (Chemical mechanical polishing) process, batch polishing has heretofore been performed to reach an intended or target remaining film thickness set value. When, at this time, a polishing pad which is brought into contact with the surface of a wafer is elastically deformed due to pressure from an underlying step at ~~a~~ an initial polishing ~~initial~~ stage, the pressure that is applied from the polishing pad increases when a pattern density is low, whereas the pressure that is applied from the polishing pad is dispersed and becomes low when the pattern density is high, thus causing a difference in the polishing rate between loose and dense wiring pattern ~~loose and dense~~ portions.

Please replace the paragraph beginning at line 23 on page 1 of the substitute specification with the following rewritten paragraph.

Thus, the remaining film thickness differences (hereinafter might be called "global steps") occur among the loose and dense wiring pattern ~~loose and dense~~ portions after polishing. Each of the global steps consists of a difference in film thickness at the loosest portion and the densest portion of the underlying wiring pattern. The global steps are different from one another according to a wiring layout. Therefore, when the global step is large in the interlayer film CMP process, the underlying wiring pattern is exposed or disappears at the loose portion of the underlying wiring pattern, and the residual step occurs due to cutting insufficiency at the dense portion of the underlying wiring pattern.

Please replace the paragraph beginning at line 24 on page 5 of the substitute specification with the following rewritten paragraph.

When the formed insulating film is planarized, global steps equivalent to ones which are obtained when the dummy ~~patterns~~ patterns provided with no pattern non-forming regions are provided, can be obtained while reducing a pattern ratio by the provision of the pattern non-forming regions at the dummy patterns.

Please replace the paragraph beginning at line 8 on page 9 of the substitute specification with the following rewritten paragraph.

Therefore, when the BPSG oxide film 16 is planarized, global steps which are equivalent to ones obtained when the conventional dummy ~~patters~~patterns are provided, can be obtained while reducing a pattern ratio by the provision of the slits 14b at the dummy patterns 14.